

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTA160N10T

1.28

0.2

0.39

2.82

RDS(• Fully ch • 100% a • Minimu perform • APPLIA • DC/DC	drain-source on-resistance: on) \leq 7.0m Ω @V _{GS} =10V haracterized avalanche voltage and avalanche tested im Lot-to-Lot variations for robust d nance and reliable operation			1 2 3 D2PA	ĸ			
-	LUTE MAXIMUM RATINGS(Ta=25	°C) VALUE	UNIT		A B	K	-	L S S
V _{DSS}	Drain-Source Voltage	100	V	c	D		Q	U
V _{GS}	Gate-Source Voltage	±30	V	- Jue	H	ſ	R	y.
ID	Drain Current-Continuous	160	А	- F++-	⊢∔G			V
I _{DM}	Drain Current-Single Pulsed	430	А	-	DIM	MIN 10	MAX	
PD	Total Dissipation @Tc=25°C	430	W		A B C	6.6	6.8 15.25	
Tj	Operating Junction Temperature	-55~175	°C		D F G	10.15 0.76 1.26	10.17 0.78 1.28	
	Storage Temperature	-55~175	°C	-	Н	1.4	1.6	
T _{stg}					J	1.33 0.4	1.35 0.6	

SYMBOL PARAMETER		MAX	UNIT			
R _{th(j-c)}	Junction-to-case thermal resistance	0.35	°C/W			

s

U

V

1.26 0.0

0.37

W 2.80



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V; ID = 250 μ A	100		V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} = V _{GS} ; ID = 250 μ A	2.5	4.5	V
R _{DS(on)}	Drain-Source On-Resistance V_{GS} =10V; I _D = 25A			7.0	mΩ
I _{GSS}	Gate-Source Leakage Current V _{GS} = ±20V;V _{DS} =0V			±200	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		5	
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 150°C		250	μA
Vsd	Diode forward voltage	I _F = 25A; V _{GS} = 0V		1.0	V

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